

Photo	<i>Name</i>
	Kozo FUJIWARA
	<i>Contacting Information</i>
	Professor, Crystal Physics Division, Institute for Materials Research Tohoku University Katahira 2-1-1, Sendai, 980-8577, Japan kozo@imr.tohoku.ac.jp
<i>Short CV (Education and Work Experience)</i>	
Educational background	
Year/Month	
1992/04 – 1996/03	Department of Materials Science & Engineering, Faculty of Engineering, Kyushu Univ. (Undergraduate)
1996/04 – 1998/03	Department of Materials Science & Engineering, Faculty of Engineering, Kyushu Univ. (Master course)
1998/04 – 2000/08	Department of Materials Science & Engineering, Faculty of Engineering, Kyushu Univ. (Doctor course)
Professional career	
2000/09 – 2008/09	Assistant professor (Crystal Physics Division), Institute for Materials Research (IMR), Tohoku Univ.
2008/10 – 2015/03	Associate professor (Crystal Chemistry Division), Institute for Materials Research (IMR), Tohoku Univ.
2015/04 –	Professor (Crystal Physics Division), Institute for Materials Research (IMR), Tohoku Univ.
<i>Awards</i>	
2003/07 Photo Contest Award (15 th American Conference on Crystal Growth)	
2005/07 Harada Young Research Award (The Honda Memorial Foundation)	
2005/08 Young Research Award (The Japanese Association for Crystal Growth)	
2011/11 Paper Award (The Japanese Association for Crystal Growth)	
2013/05 Honda Memorial Young Researcher Award (The Honda Memorial Foundation)	
<i>Research interests and activities</i>	
Crystal growth from liquid phase	
Phenomena at crystal/melt interface	
Development of crystal growth technology	
Crystal growth for photovoltaic devices	
<i>Home-page and Link to research data base</i> (Japanese text only)	

<http://www.xtalphys.imr.tohoku.ac.jp/>

Major publication

“In situ observation of interaction between grain boundaries during directional solidification of Si”, L.-C. Chuang, K. Maeda, H. Morito, K. Shiga, W. Miller and K. Fujiwara, *Scripta Materialia* **148**, 37 – 41 (2018).

“In situ observation of grain boundary groove at the crystal/melt interface in Cu”, K. Maeda, A. Niitsu, H. Morito, K. Shiga, and K. Fujiwara, *Scripta Materialia* **146**, 169 – 172 (2018).

“In situ observation of grain-boundary development from a facet-facet groove during solidification of silicon”, K. K. Hu, K. Maeda, H. Morito, K. Shiga, and K. Fujiwara, *Acta Materialia* **153**, 186–192 (2018).

“Growth mechanism of Si-faceted dendrites”, K. Fujiwara, K. Maeda, N. Usami, and K. Nakajima, *Physical Review Letters* **101**, 055503 (2008).

“Growth of structure-controlled polycrystalline silicon ingot by casting for solar cells”, K. Fujiwara, W. Pan, N. Usami, K. Sawada, M. Tokairin, Y. Nose, A. Nomura, T. Shishido, and K. Nakajima, *Acta Materialia* **54**, 3191-3197 (2006).

Present international collaborations

Anna University (India), Institute for Crystal Growth (IKZ, Berlin), National Taiwan University (Taiwan)